

WHAT IS CLAIMED IS:

1. A self-light-emitting device having an EL element, said EL element comprising:
a TFT;
a pixel electrode electrically connected to said TFT;
an EL layer formed on said pixel electrode; and
a cathode formed on said EL layer,
wherein a protective portion formed of an insulator is provided in an electrode hole.

2. A self-light-emitting device having an EL element, said EL element comprising:
a TFT;
a pixel electrode electrically connected to said TFT;
an EL layer formed on said pixel electrode; and
a cathode formed on said EL layer,
wherein a protective portion provided in an electrode hole is sandwiched between
said pixel electrode and said EL layer.

3. A self-light-emitting device having an EL element, said EL element comprising:
a TFT;
a pixel electrode electrically connected to said TFT;
an EL layer formed on said pixel electrode; and
a cathode formed on said EL layer,
wherein a protective portion provided in an electrode hole is formed of an insulator
and said EL layer is formed on surfaces of said pixel electrode and said protective portion.

4. A self-light-emitting device having an EL element, said EL element comprising:
a TFT;
a pixel electrode electrically connected to said TFT;
an EL layer formed on said pixel electrode; and
a cathode formed on said EL layer,
wherein said EL layer and a protective portion are sandwiched between said pixel electrode and said cathode.

5. A self-light-emitting device having an EL element, said EL element comprising:
a TFT;
a pixel electrode electrically connected to said TFT;
an EL layer formed on said pixel electrode; and
a cathode formed on said EL layer,
wherein a plurality of said pixel electrodes are formed in a pixel portion and a protective portion is formed in a space between said pixel electrodes.

6. A self-light-emitting device according to any one of claims 1 to 5, wherein a surface of said pixel electrode and a surface of said protective portion are planarized to be flush with each other.

7. An electric equipment, which uses a self-light-emitting device according to any one of claims 1 to 5, as a display portion or a light source.

8. A method of manufacturing a self-light-emitting device comprising the steps of:
forming on a substrate a TFT and a pixel electrode electrically connected to said
TFT;
forming an insulating film on said pixel electrode; and
forming a protective portion by selectively etching said insulating film.

9. A method of manufacturing a self-light-emitting device comprising the steps of:
forming on a substrate a TFT and a pixel electrode electrically connected to said
TFT;
forming an organic resin film on said pixel electrode; and
forming a protective portion by selectively etching said organic resin film.

10. A method of manufacturing a self-light-emitting device comprising the steps of:
forming on a substrate a TFT and a pixel electrode electrically connected to said
TFT;
forming an organic resin film on said pixel electrode; and
forming a protective portion in an electrode hole and in a space between said pixel
electrodes by selectively etching said organic resin film.

11. A self-light emitting device comprising:
at least two first electrodes formed over a substrate with a gap between said first
electrodes;
an insulating layer formed in the gap between said first electrodes;
an EL layer formed on said first electrodes and said insulating layer; and

a second electrode opposed to said at least two first electrodes with said EL layer interposed therebetween.

12. The self-light emitting device according to claim 11 wherein said first electrodes function as an anode while said second electrode functions as a cathode.

13. The self-light emitting device according to claim 11 wherein said self-light emitting device is a passive display device.

14. The self-light emitting device according to claim 11 wherein said EL layer comprises an organic electroluminescence material.

15. A self-light emitting device comprising:
at least one switching element;
at least one interlayer insulating film formed over said switching element;
a contact hole opened in said switching element;
a pixel electrode formed on said interlayer insulating film and electrically connected to said switching element through said contact hole;
an insulating layer formed on a portion of said pixel electrode in said contact hole;
an EL layer formed on said pixel electrode and said insulating layer; and
a second electrode formed on said EL layer.

16. The self-light emitting device according to claim 15 wherein said switching element comprises a thin film transistor.

17. The self-light emitting device according to claim 15 wherein said switching element comprises a transistor formed within a silicon substrate.

18. The self-light emitting device according to claim 15 wherein said pixel electrode is an anode while said second electrode is a cathode.

19. The self-light emitting device according to claim 15 wherein said pixel electrode is a cathode while said second electrode is an anode.

20. The self-light emitting device according to claim 15 wherein said EL layer comprises at least one organic EL layer.

21. The self-light emitting device according to claim 15 wherein said a surface of said insulating layer is substantially flush with a surface of said pixel electrode.

22. A self-light emitting device comprising:
at least first and second switching elements;
at least one interlayer insulating film formed over said first and second switching elements;
at least first and second pixel electrodes formed over said interlayer insulating film wherein said first and second pixel electrodes are electrically connected to said first and second switching elements, respectively;
an insulating layer formed in a gap between said first and second pixel electrodes;

an EL layer formed on said first and second pixel electrodes and said insulating layer; and

a third electrode formed on said EL layer opposed to said first and second pixel electrodes.

23. The self-light emitting device according to claim 22 wherein said switching element comprises a thin film transistor.

24. The self-light emitting device according to claim 22 wherein said switching element comprises a transistor formed within a silicon substrate.

25. The self-light emitting device according to claim 22 wherein each of said first and second pixel electrodes is an anode while said third electrode is a cathode.

26. The self-light emitting device according to claim 22 wherein each of said first and second pixel electrodes is a cathode while said third electrode is an anode.

27. The self-light emitting device according to claim 22 wherein said EL layer comprises at least one organic EL layer.

28. The self-light emitting device according to claim 22 wherein a surface of said insulating layer is substantially flush with a surface of said first and second pixel electrodes.

29. An electronic device having the self-light emitting device according to claim 11.

30. An electronic device having the self-light emitting device according to claim 15.

31. An electronic device having the self-light emitting device according to claim 22.

32. An electronic device according to claim 29 wherein said electronic device is selected from the group consisting of a video camera, a head mounted EL display, an image playback device, a portable computer, a personal computer, a cellular phone and an audio playback device.

33. An electronic device according to claim 30 wherein said electronic device is selected from the group consisting of a video camera, a head mounted EL display, an image playback device, a portable computer, a personal computer, a cellular phone and an audio playback device.

34. An electronic device according to claim 31 wherein said electronic device is selected from the group consisting of a video camera, a head mounted EL display, an image playback device, a portable computer, a personal computer, a cellular phone and an audio playback device.